



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	2Ω @ $V_{GS} = 4.5V$	350mA
60 V	2.5Ω @ $V_{GS} = 2.5V$	330IIIA

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions

Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

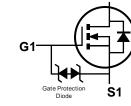
- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)

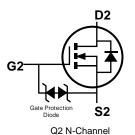


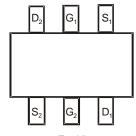


Top View

SOT363







Equivalent Circuit

Top View Pin out

Ordering Information (Note 4)

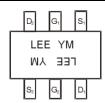
Part Number	Case	Packaging
DMN62D0UDW-7	SOT363	3000/Tape & Reel
DMN62D0UDW-13	SOT363	10000/Tape & Reel

Q1 N-Channel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



LEE = Product Type Marking Code YM = Date Code Marking Y or Y = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

Year	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027
Code	D	Е	F	G	Н		J	K	Г	М	N	0
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	60	V	
Gate-Source Voltage		V _{GSS}	±20	V	
Continuous Drain Current (Note 6) $V_{GS} = 4.5V$ Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			I _D	350 290	mA
Maximum Continuous Body Diode Forward Curren	t (Note 6)	Is	0.4	А	

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_{D}	320	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	400	°C/W
Total Power Dissipation (Note 6)		P_{D}	410	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	312	°C/W
Operating and Storage Temperature Range		$T_{J_{I}}T_{STG}$	-55 to +150	°C

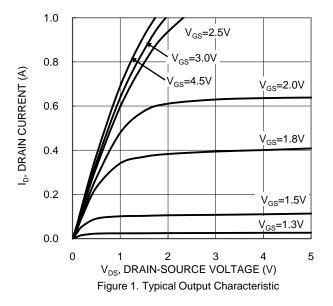
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

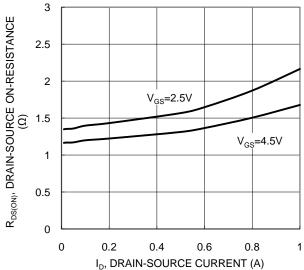
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_		1.0	μΑ	$V_{DS} = 60V$, $V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.5	_	1.0	V	$V_{DS} = 10V, I_D = 250\mu A$
			1.2	2.0		$V_{GS} = 4.5V, I_D = 0.1A$
Static Drain-Source On-Resistance	R _{DS(ON)}		1.4 1.8	2.5	Ω	$V_{GS} = 2.5V, I_D = 0.05A$
	, ,			3.0		$V_{GS} = 1.8V, I_D = 0.05A$
Forward Transconductance	Y _{fs}	_	1.8	_	S	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage	V _{SD}	_	0.8	1.3	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)				•	•	
Input Capacitance	Ciss	_	32	_	pF	.,
Output Capacitance	Coss	_	3.9	-	рF	$V_{DS} = 30V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	2.4	_	pF	1 = 1.000112
Gate Resistance	R_g	_	101	_	Ω	$f = 1MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$
Total Gate Charge	Qg	_	0.5	_	nC	451/1/ 401/
Gate-Source Charge	Q _{gs}	_	0.09	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$
Gate-Drain Charge	Q _{qd}	_	0.09	_	nC	I _D = 250mA
Turn-On Delay Time	t _{D(ON)}	_	2.4	_	ns	
Turn-On Rise Time	t _R	_	2.5	-	ns	$V_{DD} = 30V, V_{GS} = 10V,$
Turn-Off Delay Time	t _{D(OFF)}	_	22.6	_	ns	$R_G = 25\Omega$, $I_D = 200 \text{mA}$
Turn-Off Fall Time	t _F	_	12.5	_	ns	

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
- 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.







I_D, DRAIN-SOURCE CURRENT (A)
Figure 3. Typical On-Resistance vs. Drain Current and
Gate Voltage

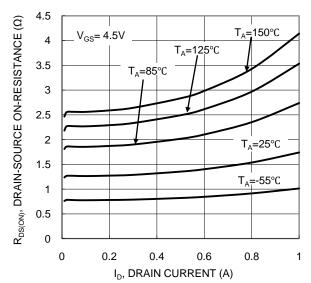
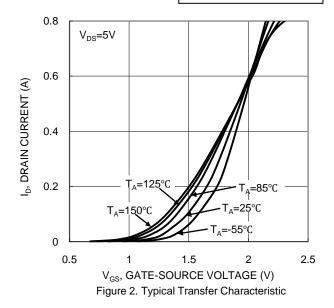
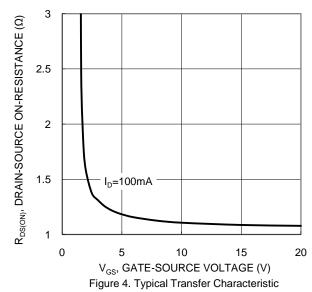


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





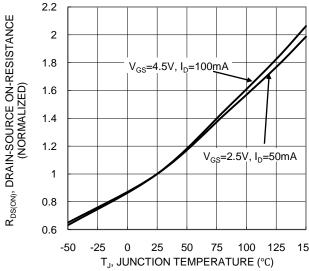
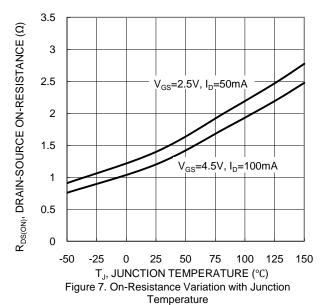
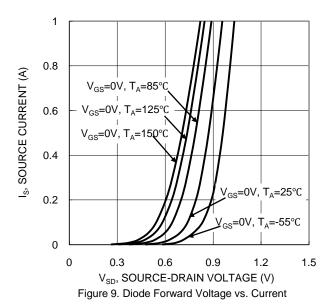
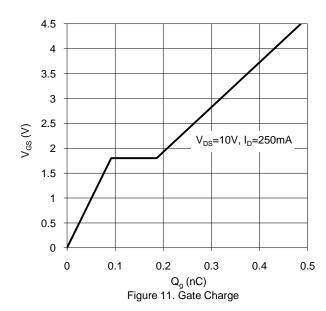


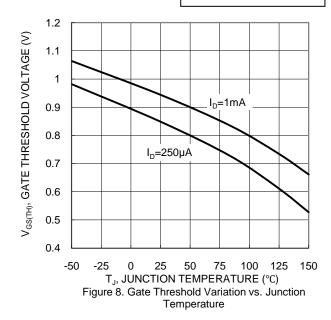
Figure 6. On-Resistance Variation with Junction Temperature

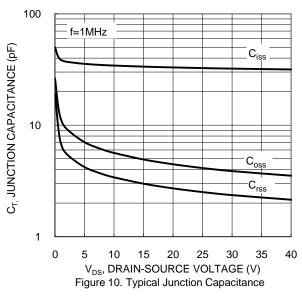


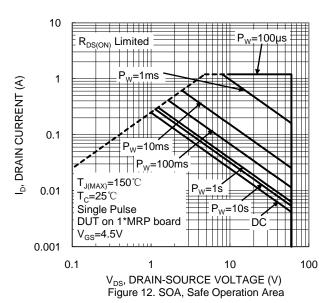














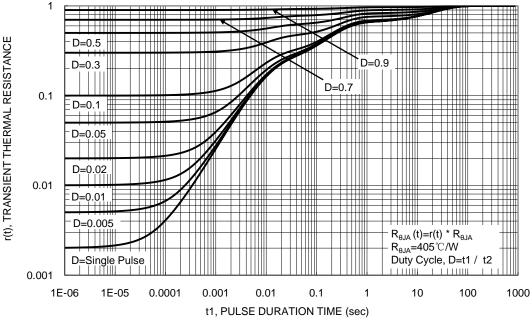


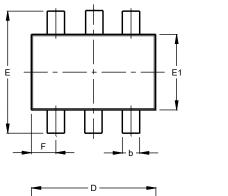
Figure 13. Transient Thermal Resistance

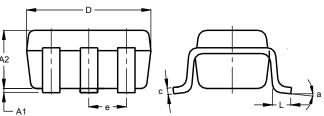


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



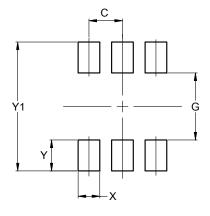


SOT363						
Dim	Min Max Typ					
A1	0.00	0.10	0.05			
A2	0.90	1.00	1.00			
b	0.10	0.30	0.25			
С	0.10	0.22	0.11			
D	1.80	2.20	2.15			
Е	2.00	2.20	2.10			
E1	1.15	1.35	1.30			
е	0.650 BSC					
F	0.40	0.45	0.425			
L	0.25	0.40	0.30			
а	0°	8°				
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



Dimensions	Value (in mm)				
С	0.650				
G	1.300				
Х	0.420				
Y	0.600				
Y1	2.500				



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